

Silicon NPN transistor in a TO-92 Plastic Package.

High  $f_T$ , low output capacitance, low base time constant and high gain, excellent noise characteristics.

FM radio RF amplifier applications.

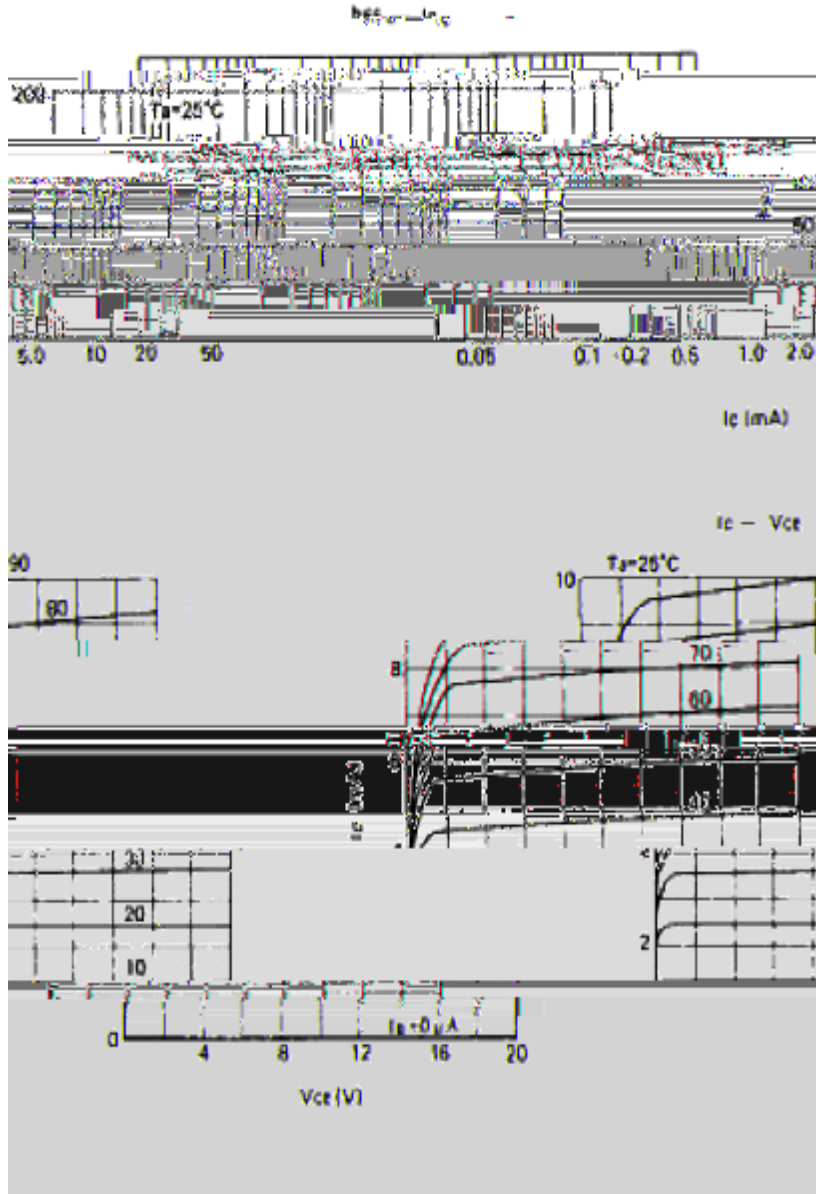


PIN1

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	25	V
Collector to Emitter Voltage	$V_{CEO}$	20	V
Emitter to Base Voltage	$V_{EBO}$	4.0	V
Collector Current - Continuous	$I_C$	20	mA
Collector Power Dissipation	$P_C$	150	mW
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=10\text{ A}$	25			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0\text{mA}$	20			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=10\text{ A}$	4.0			V

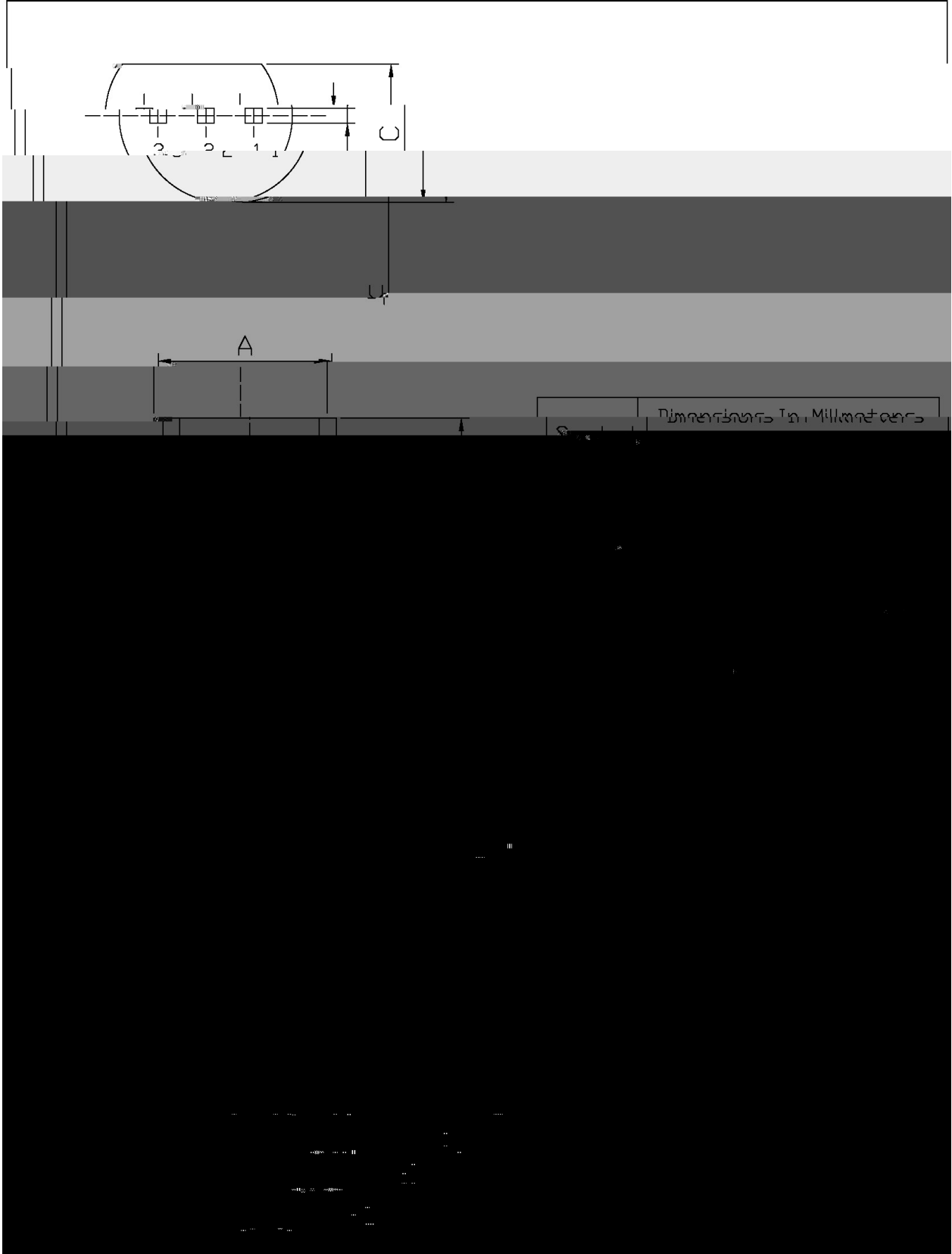
/ Electrical Characteristic Curve



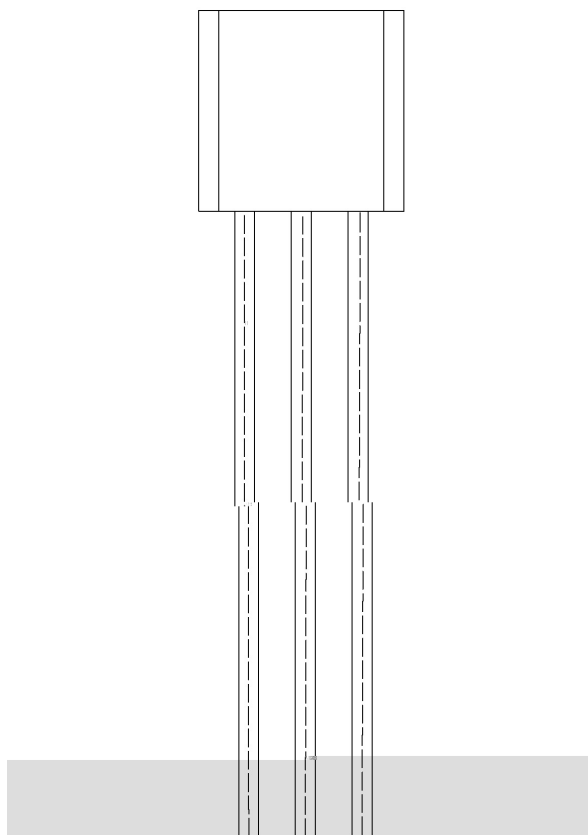
/ Package Dimensions

TO-92

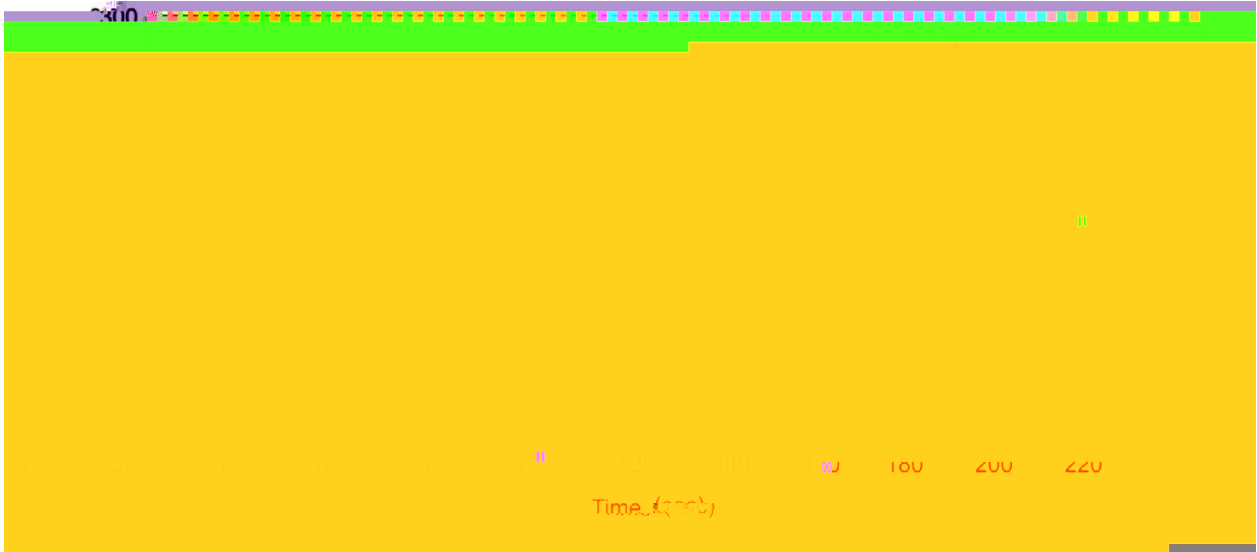
Unit: mm



**/ Marking Instructions**



**( ) / Temperature Profile for Dip Soldering(Pb-Free)**



- |   |     |     |    |          |       |   |
|---|-----|-----|----|----------|-------|---|
| 1 | 25  | 150 | 60 | 90sec;   | Note: | 1.Preheating:25~150 , Time:60~90sec.    |
| 2 | 255 | 5   | 5  | 0.5sec;  |       | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 |     |     | 2  | 10 /sec. |       | 3. Cooling Speed: 2~10 /sec.            |

**/ Resistance to Soldering Heat Test Conditions**

270 5                      10 1 sec.                      Temp:270±5                      Time:10±1 sec

**/ Packaging SPEC.**

/ BULK

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm3)
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